

① 0 Ch. 4, Q. 5

With thermal conduction,  $\bar{e}$ 's at one end of the sample have more energy than  $\bar{e}$ 's at the other end. More energetic  $\bar{e}$ 's diffuse down the  $T$  gradient, carrying a net energy flux.

On average, there is no particle or charge buildup which would be quite unfavorable energetically.

② 0 Ch. 4, Q. 8

The Hall constant is defined as

$R_H \equiv \frac{E_H}{J_x B}$ , where  $E_H$  is the Hall field,  $B$  is the external magnetic field, and  $J_x$  is the current density. Since  $J_x \sim N$ , ( $\bar{e}$  conc'n)

$$R_H \sim \frac{1}{N}$$

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③ 0 Ch. 4, Pr. 10

$$V_c = \frac{\hbar \omega_c}{2\pi} = 2.8 B \text{ GHz} \quad \text{for } m^* = m_0, \quad \text{the free } \bar{e} \text{ mass}$$

↑  
in kG

Then  $V_c = 24 \text{ GHz}$  gives

$$B = \frac{24}{2.8} \approx 8.6 \text{ kG.}$$

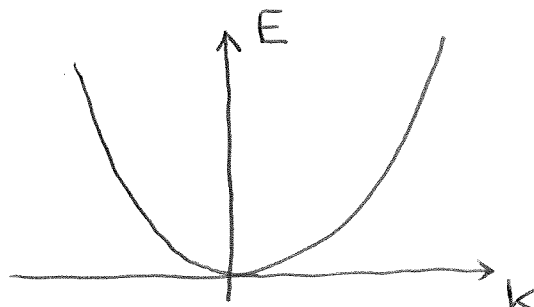
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④ 0 Ch. 5, Q. 2

For a truly free  $\bar{e}$ ,

$$\begin{cases} \psi_k^{(0)} = \frac{1}{\sqrt{L}} e^{ikx} \\ E_k^{(0)} = \frac{\hbar^2 k^2}{2m_0} \end{cases}, \quad \leftarrow \textcircled{1d}$$

This leads to a single dispersion curve:



"Cutting & pasting" is not justifiable here because there is no periodicity of the lattice:

$$E_k = E_{k+G}, \quad G = \frac{2\pi n}{a}, \quad n = 0, \pm 1, \pm 2, \dots$$

Thus the difference between empty lattice & free space is that we impose symmetry properties in  $k$ -space (even though there is no potential) in the former case. These symmetries follow from the translational symmetry of the real lattice.

⑤. 0. Ch. 5, Pr. 12      ①D

$$a) \quad k = \frac{2\pi}{L} n \quad \Rightarrow \quad N = \frac{k}{(2\pi/L)} = \frac{Lk}{2\pi}$$

↑  
# states with  $\leq k$

$$\frac{dN}{dk} = \frac{L}{2\pi} = \frac{1}{2\pi} \quad \text{if } L=1$$

$$g(E) = \frac{dN}{dE} = \frac{dN}{dk} \frac{dk}{dE} = \frac{1/2\pi}{(dE/dk)}$$

b) TB model: (5.43)  
in ①

$$E(k) = E_0 + 4\gamma \sin^2\left(\frac{ka}{2}\right)$$

Then

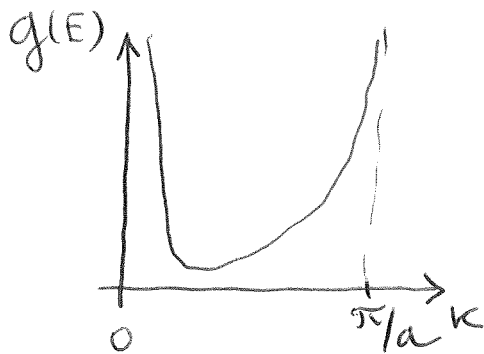
$$\begin{aligned} \frac{dE}{dk} &= 8\gamma \sin\left(\frac{ka}{2}\right) \cos\left(\frac{ka}{2}\right) \times \frac{a}{2} = \\ &= 2\gamma a \sin(ka) \end{aligned}$$

$$\text{So, } g(E) = \frac{1/2\pi}{2\gamma a \sin(ka)}$$

Limits:

$$k \rightarrow 0 : g(E) \sim \frac{1}{k} \sim \frac{1}{\sqrt{E(k) - E_0}}$$

$$k \rightarrow \frac{\pi}{a} : g(E) \rightarrow \infty$$



⑥ 8 Ch. 5, Pr. 14

a) Free  $\bar{e}$  model:

$$n = \underset{\substack{\uparrow \\ \text{spin}}}{2} \frac{1}{(2\pi)^3} \frac{4}{3} \pi k_F^3 = \frac{1}{3\pi^2} k_F^3, \text{ or}$$
$$k_F = \underline{\underline{(3\pi^2 n)^{1/3}}}$$

b) Fermi sphere will touch the face of the 1st BZ when

$k_F = k_i$ , where

$$\vec{k}_i = \frac{1}{2} \vec{a} \text{ for fcc, and}$$

(or  $\frac{1}{2} \vec{b}, \frac{1}{2} \vec{c}$ )

$$\left\{ \begin{array}{l} \vec{a} = \frac{2\pi}{a} (1, -1, 1) \\ \vec{b} = \frac{2\pi}{a} (1, 1, -1) \\ \vec{c} = \frac{2\pi}{a} (-1, 1, 1) \end{array} \right.$$

Then  $k_i = \frac{1}{2} \frac{25\pi}{a} \sqrt{1^2 + 1^2 + 1^2} = \frac{\sqrt{3}\pi}{a}$ .

For fcc, the # of atoms is

$\frac{4}{a^3}$  & the # of  $\bar{e}$ 's is  
(per unit volume)

$\frac{4}{a^3} \quad \frac{n}{n_a}$

$\bar{e}$ -to-atom ratio

Then

$(3\pi^2 \frac{4}{a^3} \frac{n}{n_a})^{1/3} = \frac{\sqrt{3}\pi}{a}$ , or

$\frac{n}{n_a} = \frac{1}{12\pi^2} 3^{3/2} \pi^3 = \frac{\sqrt{3}\pi}{4} = 1.36$ .

c) Zn trivalent  
Cu monovalent

$\bar{e}$  concentr'n  $n = \frac{4}{a^3} \{ (1-x) \times 1 + \underset{\substack{\uparrow \\ \text{Zn fraction}}}{x} \times 2 \} = \frac{4}{a^3} (1+x)$ .

$k_F = k_i$  as in (b):

$(3\pi^2 n)^{1/3} = \frac{\sqrt{3}\pi}{a}$ , or

$(12\pi^2)^{1/3} (1+x)^{1/3} = \sqrt{3}\pi$ ,

$(\frac{12}{\pi})^{1/3} (1+x)^{1/3} = \sqrt{3} \Rightarrow 1+x = \frac{\pi}{12} 3\sqrt{3} =$

$= \frac{\pi\sqrt{3}}{4} \Rightarrow x = \frac{\sqrt{3}\pi}{4} - 1 = 0.36$ ,

consistent with (b).

$$(7) \quad m \left( \frac{dv}{dt} + \frac{v}{\tau} \right) = -eE,$$

$$\begin{cases} v = v_0 e^{-i\omega t} \\ E = E_0 e^{-i\omega t} \end{cases} \text{ give}$$

$$m \left( -i\omega v_0 + \frac{v_0}{\tau} \right) = -eE_0, \text{ or}$$

$$v_0 = \frac{-eE_0/m}{-i\omega + 1/\tau} = -\frac{eE_0\tau}{m} \frac{1}{-i\omega\tau + 1} =$$

$$= -\frac{eE_0\tau}{m} \frac{1+i\omega\tau}{1+\omega^2\tau^2}.$$

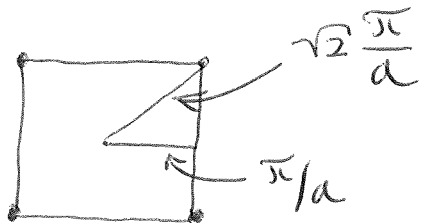
Then

$$j = -nev = \frac{ne^2\tau}{m} E \frac{1+i\omega\tau}{1+\omega^2\tau^2},$$

so that

$$\sigma(\omega) = \underbrace{\sigma_0}_{\frac{ne^2\tau}{m}} \frac{1+i\omega\tau}{1+\omega^2\tau^2}.$$

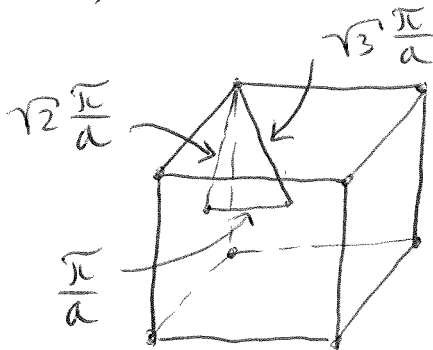
8. a) 2D square lattice



$$k_{\text{corner}} = \sqrt{2} k_{\text{center}}$$

$$E \sim k^2 \Rightarrow E_{\text{corner}} = 2 E_{\text{center}}$$

b) 3D SC lattice



$$k_{\text{corner}} = \sqrt{3} k_{\text{center}},$$

$$E_{\text{corner}} = 3 E_{\text{center}}$$

c) If  $E_{\text{gap}} < E_{\text{corner}} - E_{\text{center}}$ ,

$\bar{e}$ 's will start occupying center states in 2nd BZ rather than corner states in 1<sup>st</sup> BZ.

If this is the case, divalent ~~elements~~ elements can become metals rather than insulators.

⑨ Photonic crystals are devices in which a distribution of refractive indices is chosen such that incoming light waves become standing waves due to refraction & reflection. This makes them analogous to semiconductor devices, except light waves are used instead of  $\bar{e}$  waves. Some of the challenges are:

- a) identifying & building structures out of them suitable materials (with necessary optical properties)
- b) the devices must be able to handle incoming waves coming in all directions

Potential uses: lasers, fiber optics